DATE: June 1, 1998

# **Manual Update Sheet**

Document Being Updated: TMS320C5x User's Guide

Literature Number Being Updated: SPRU056C

Manual Included in a Kit: Yes

This Manual Update Sheet (SPRZ113A) ships with the TMS320C5x User's Guide.

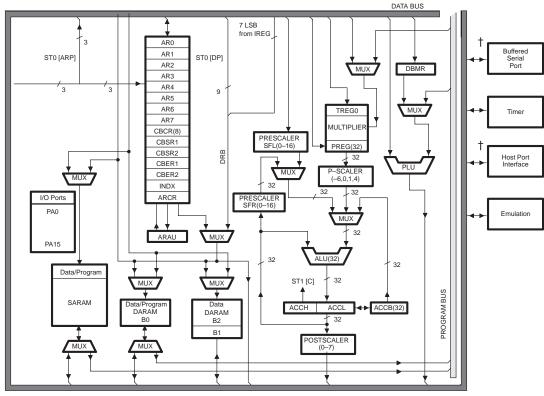
Updates within paragraphs appear in a **bold typeface**.

## Page: Change or Add:

3–3

In the bottom half of Figure 3–1, the auxiliary register file MUX output now connects with the trailing wire bus found on the data bus.





Notes: All registers and data lines are 16-bits wide unless otherwise specified. DATA BUS †Not available on all devices.

4–11 In Table 4–5, change the reset values for the ARP bit and the OVM bit so both have a reset value of "X." In other words, there is no reset value for the ARP bit and the OVM bit.

Table 4–5. Status Register 0 (ST0) Bit Summary

Bit	Name	Reset value	Function	
15–13	ARP	х	indirect addr the auxiliary ence instruc	ister pointer. These bits select the auxiliary register (AR) to be used in ressing. When the ARP is loaded, the previous ARP value is copied to register buffer (ARB) in ST1. The ARP can be modified by memory-refer- tions when you use indirect addressing, and by the MAR or LST #0 When an LST #1 instruction is executed, the ARP is loaded with the same ARB.
11	OVM	x		ode bit. This bit enables/disables the accumulator overflow saturation arithmetic logic unit (ALU). The OVM bit can be modified by the LST #0
			OVM = 0	Disabled. An overflowed result is loaded into the accumulator without modification. The OVM bit can be cleared by the CLRC OVM instruction.
			OVM = 1	Overflow saturation mode. An overflowed result is loaded into the ac- cumulator with either the most positive (00 7FFF FFFFh) or the most negative value (FF 8000 0000h). The OVM bit can be set by the SETC OVM instruction.

4–12

In Table 4–5, change the reset value for the DP bit so it has a reset value of "X." In other words, there is no reset value for the DP bit.

Bit	Name	Reset value	Function
8–0	DP	X	Data memory page pointer bits. These bits specify the address of the current data memory page. The DP bits are concatenated with the 7 LSBs of an instruction word to form a direct memory address of 16 bits. The DP bits can be modified by the LST #0 or LDP instruction.

 Table 4–5.
 Status Register 0 (ST0) Bit Summary (Continued)

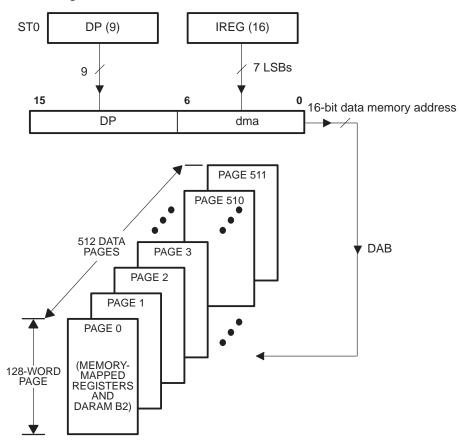
4–13 In Table 4–6, change the reset value for the ARB bit and the TC bit so they have no reset value.

Bit	Name	Reset value	Function
15–13	ARB	X	Auxiliary register buffer. This 3-bit field holds the previous value contained in the auxiliary register pointer (ARP) in ST0. Whenever the ARP is loaded, the previous ARP value is copied to the ARB, except when using the LST #0 instruction. When the ARB is loaded using the LST #1 instruction, the same value is also copied to the ARP. This is useful when restoring context (when not using the automatic context save) in a subroutine that modifies the current ARP.
11	TC	x	Test/control flag bit. This 1-bit flag stores the results of the arithmetic logic unit (ALU) or parallel logic unit (PLU) test bit operations. The TC bit is affected by the APL, BIT, BITT, CMPR, CPL, NORM, OPL, and XPL instructions. The status of the TC bit determines if the conditional branch, call, and return instructions execute. The TC bit can be modified by the LST #1 instruction.

Table 4–6. Status Register 1 (ST1) Bit Summary

5–2 In Figure 5–1, change the page 0 length to "128-WORD PAGE."

Figure 5–1. Direct Addressing



5–22 In Example 5–13, add two new lines at the beginning of the example.

Example 5–13. Circular Addressing

mar ldp	•		
splk	#203h,CBER1	;	Circular buffer start register Circular buffer end register Enable AR6 pointing to buffer 1
lar lacc	ar6,#200h *		Case 1 AR6 = 200h
lar lacc	ar6,#203h *		Case 2 AR6 = 203h
lar lacc	ar6,#200h *+		Case 3 AR6 = 201h
	ar6,#203h *+		Case 4 AR6 = 200h
lar lacc	ar6,#200h *-		Case 5 AR6 = 1FFh
	ar6,#203h *-		Case 6 AR6 = 200h
lar adrk	ar6,#202h 2		Case 7 AR6 = 204h
lar adrk	ar6,#203h 2		Case 8 AR6 = 200h

## Page: Change or Add: 6-32 Change the second operand for the ADD instruction. **Operands** $0 \leq \text{shift} \leq 16$ (defaults to 0) 6-44 Change the fourth operand for the AND instruction. Operands $0 \le \text{shift} \le 16$ Change the operand for the BSAR instruction. 6-83 Operands $1 \leq \text{shift} \leq 16$ 6-85 Change the description for the CALAD instruction. Description The current program counter (PC) is incremented by 3 and pushed onto the top of the stack (TOS). Then, the one 2-word instruction or two 1-word instructions following the CALAD instruction are fetched from program memory and executed before the call is executed. Then, the contents of the accumulator low byte (ACCL) are loaded into the PC. Execution continues at this address. The CALAD instruction is used to perform computed subroutine calls. CALAD is a branch and call instruction (see Table 6-8). 6-87 Change the description for the CALLD instruction. The current program counter (PC) is incremented by 4 and pushed onto Description the top of the stack (TOS). Then, the one 2-word instruction or two 1-word instructions following the CALLD instruction are fetched from program memory and executed before the call is executed. The program memory address (pma) is loaded into the PC. Execution continues at this address. The current auxiliary register (AR) and auxiliary register pointer (ARP) are modified as specified. The pma can be either a symbolic or numeric address. CALLD is a branch and call instruction (see Table 6-8).

6–91 Change the description for the CCD instruction.

Description If the specified conditions are met, the current program counter (PC) is incremented by 4 and pushed onto the top of the stack (TOS).

Then, the one 2-word instruction or two 1-word instructions following the CCD instruction are fetched from program memory and executed before the call is executed.

Then, the program memory address (pma) is loaded into the PC. Execution continues at this address. The pma can be either a symbolic or numeric address. Not all combinations of the conditions are meaningful. In addition, the NTC, TC, and BIO conditions are mutually exclusive.

If the specified conditions are not met, control is passed to the next instruction.

The CCD functions in the same manner as the CALLD instruction (page 6–87) if all conditions are true. CCD is a branch and call instruction (see Table 6–8).

6–103 Change the opcode for the CRLT instruction to reflect the new values for bits 2, 1, and 0.

Opcode	15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0
•	1	0	1	1	1	1	1	0	0	0	0	1	1	1	0	0

6–115 Change the third operand for the LACC instruction.

Operands

 $0 \le \text{shift} \le \mathbf{16}$  (defaults to 0)

6–127 Change the table Cycles for a Single Instruction (short immediate addressing).

Cycles for a Single Instruction (short immediate addressing)

Operand	ROM	DARAM	SARAM	External Memory
	2	2	2	2+p <sub>code</sub>

6–129 Change the table Cycles for a Single Instruction (short immediate addressing).

Cycles for a Single Instruction (short immediate addressing)									
Operand	ROM	DARAM	SARAM	External Memory					
	2	2	2	2+p <sub>code</sub>					

6–188 Change the fourth operand for the OR instruction.

#### **Operands** $0 \le \text{shift} \le 16$

6–261 Change the second operand for the SUB instruction.

#### **Operands** $0 \le \text{shift} \le 16 \text{ (defaults to 0)}$

6–278 Change the data memory address in Example 1 from 1905h to 1005h.

6–282 Change the fourth operand for the XOR instruction.

**Operands**  $0 \le \text{shift} \le 16$ 

- 8–6 In Figure 8–6, change the word Off-chip to Reserved on the Program memory map for the range from 0040h to 8000h.
- 8–11 In Table 8–6, change the values in the Off-Chip column for the first and fifth rows.

	Bit values		ROM	SARAM	DARAM BO	
CNF	RAM	MP/MC	(2K-words)	(6K-words)	(512-words)	Off-Chip
0	0	0	0000–07FF	Off-chip	Off-chip	8000-FFFF
1	0	0	0000–07FF	Off-chip	FE00–FFFF	8000-FDFF

Table 8–6. 'C57S Program Memory Configuration

8–32 Change the last sentence in the fourth bullet.

- 32K words of global data memory are enabled initially in data spaces 8000h to FFFFh. After the code transfer is complete, the global memory is disabled before control is transferred to the destination address in program memory.
- 9–10 In Table 9–4, change the sentences after Soft=0 and Soft=1. Also, add a sentence to the TSS register.

Table 9–4. Til	mer Control Register	(TCR) Bit Summary
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Bit	Name	Reset value	Function	
11	Soft	0		ised in conjunction with the Free bit to determine the state of the timer t is encountered. When the Free bit is cleared, the Soft bit selects the mode.
			Soft = 0	The timer stops immediately.
			Soft = 1	The timer stops after decrementing to zero.
4	TSS	0	bit is cleare implement	status bit. This bit stops or starts the on-chip timer. At reset, the TSS d and the timer immediately starts timing. Note that due to timer logic tation, two successive writes of one to the TSS bit are required to top the timer.

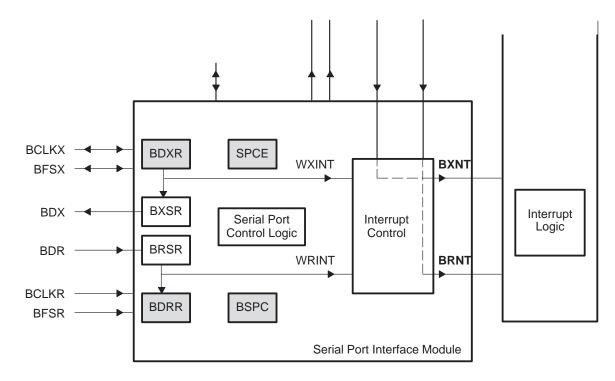
9–11

Delete the last sentence in the Notes section and replace it with the sentence indicated.

The current value in the timer can be read by reading the TIM; the PSC can be read by reading the TCR. Because it takes two instructions to read both registers, there may be a change between the two reads as the counter decrements. Therefore, when making precise timing measurements, it may be more accurate to stop the timer to read these two values. **Due to timer logic implementation, two instructions are also required to properly stop the timer; therefore, two successive writes of one to the TSS bit should be made when the timer must be stopped.** 

9–62 Change the XINT and RINT labels found in the lower right portion of Figure 9–35.

Figure 9–35. ABU Block Diagram

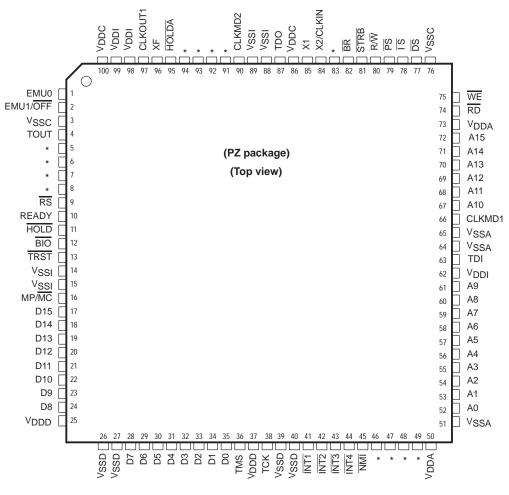


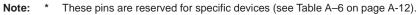
9–63 Change the last sentence in the first paragraph.

The internal 'C5X memory used for autobuffering consists of a 2K-word block of single-access memory that can be configured as data, program, or both (as with other single-access memory blocks). This memory can also be used by the CPU as general purpose storage, however, this is the only memory block in which autobuffering can occur. Since the BSP is implemented on several different TMS320 devices, the actual base address of the ABU memory may not be the same in all cases. The 2K-word block of BSP memory is located at 800h–FFFh in data memory or at 8000h–87FFh in program memory as specified by the RAM and OVLY control bits.

A–4 In Figure A–2, change the signal name on pin 80 to  $R/\overline{W}$ .

Figure A-2. Pin/Signal Assignments for the 'C51, 'C52, 'C53S, and 'LC56 in 100-Pin TQFP





A–6 In Figure A–3, change the signal name on pin 108 to X2/CLKIN.

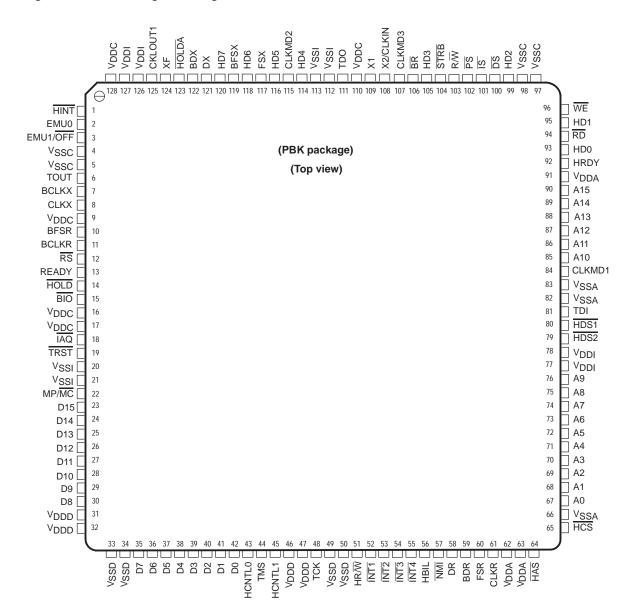


Figure A–3. Pin/Signal Assignments for the 'LC57 in 128-Pin TQFP

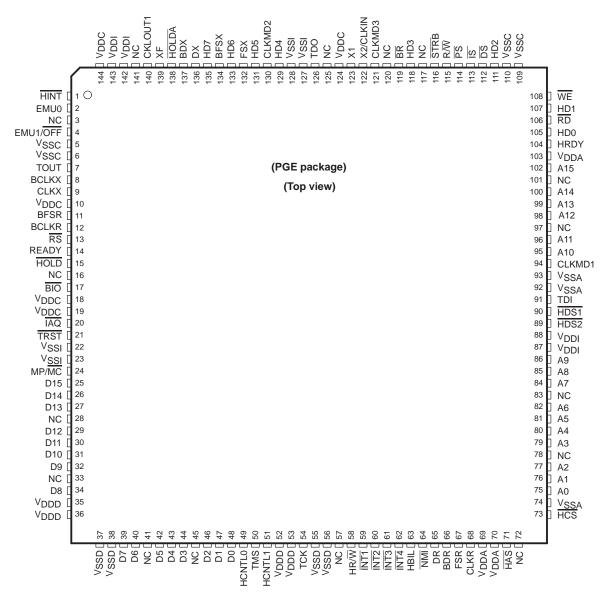
A–7 In Table A–3, change the signal name on pin 108 to X2/CLKIN and reorder the signal names.

Signal	Pin	Signal	Pin	Signal	Pin	Signal	Pin	Signal	Pin
A0	67	CLKMD3	107	FSX	117	IS	101	V <sub>DDD</sub>	47
A1	68	CLKOUT1	125	HAS	64	MP/MC	22	V <sub>DDI</sub>	77
A2	69	CLKR	61	HBIL	56	NMI	57	V <sub>DDI</sub>	78
A3	70	CLKX	8	HCNTL0	43	PS	102	V <sub>DDI</sub>	126
A4	71	D0	42	HCNTL1	45	RD	94	V <sub>DDI</sub>	127
A5	72	D1	41	HCS	65	READY	13	V <sub>SSA</sub>	66
A6	73	D2	40	HD0	93	RS	12	V <sub>SSA</sub>	82
A7	74	D3	39	HD1	95	R/W	103	V <sub>SSA</sub>	83
A8	75	D4	38	HD2	99	STRB	104	V <sub>SSC</sub>	4
A9	76	D5	37	HD3	105	тск	48	V <sub>SSC</sub>	5
A10	85	D6	36	HD4	114	TDI	81	V <sub>SSC</sub>	97
A11	86	D7	35	HD5	116	TDO	111	V <sub>SSC</sub>	98
A12	87	D8	30	HD6	118	TMS	44	V <sub>SSD</sub>	33
A13	88	D9	29	HD7	120	TOUT	6	V <sub>SSD</sub>	34
A14	89	D10	28	HDS1	80	TRST	19	V <sub>SSD</sub>	49
A15	90	D11	27	HDS2	79	V <sub>DDC</sub>	9	V <sub>SSD</sub>	50
BCLKR	11	D12	26	HINT	1	V <sub>DDA</sub>	91	V <sub>SSI</sub>	20
BCLKX	7	D13	25	HOLD	14	V <sub>DDA</sub>	63	V <sub>SSI</sub>	21
BDR	59	D14	24	HOLDA	123	V <sub>DDA</sub>	62	V <sub>SSI</sub>	112
BDX	122	D15	23	HRDY	92	V <sub>DDC</sub>	16	V <sub>SSI</sub>	113
BFSR	10	DR	58	HR/W	51	V <sub>DDC</sub>	17	WE	96
BFSX	119	DS	100	IAQ	18	V <sub>DDC</sub>	110	X1	109
BIO	15	DX	121	INT1	52	V <sub>DDC</sub>	128	X2/CLKIN	108
BR	106	EMU0	2	INT2	53	V <sub>DDD</sub>	31	XF	124
CLKMD1	84	EMU1/OFF	3	INT3	54	V <sub>DDD</sub>	32		
CLKMD2	115	FSR	60	INT4	55	V <sub>DDD</sub>	46		

Table A–3. Signal/Pin Assignments for the 'LC57 in 128-Pin TQFP

A–10 In Figure A–5, correct the signal names for pins 1–16, 28–45, 57–71, and 78–141; change the signal name on pin 122 to X2/CLKIN.





**Note:** NC These pins are not connected (reserved).

A–11

In Table A–5, correct the signal names for pins 1–16, 28–45, 57–71, and 78–141; change the signal name on pin 122 to X2/CLKIN; reorder the signal names.

Signal	Pin	Signal	Pin	Signal	Pin	Signal	Pin	Signal	Pin
A0	75	CLKX	9	HD0	105	тск	54	V <sub>SSD</sub>	37
A1	76	D0	48	HD1	107	TDI	91	V <sub>SSD</sub>	38
A2	77	D1	47	HD2	111	TDO	126	V <sub>SSD</sub>	55
A3	79	D2	46	HD3	118	TMS	50	V <sub>SSD</sub>	56
A4	80	D3	44	HD4	129	TOUT	7	V <sub>SSI</sub>	22
A5	81	D4	43	HD5	131	TRST	21	V <sub>SSI</sub>	23
A6	82	D5	42	HD6	133	V <sub>DDA</sub>	69	V <sub>SSI</sub>	127
A7	84	D6	40	HD7	135	V <sub>DDA</sub>	70	V <sub>SSI</sub>	128
A8	85	D7	39	HDS1	90	V <sub>DDA</sub>	103	WE	108
A9	86	D8	34	HDS2	89	V <sub>DDC</sub>	10	X1	123
A10	95	D9	32	HINT	1	V <sub>DDC</sub>	18	X2/CLKIN	122
A11	96	D10	31	HOLD	15	V <sub>DDC</sub>	19	XF	139
A12	98	D11	30	HOLDA	138	V <sub>DDC</sub>	124	†	3
A13	99	D12	29	HRDY	104	V <sub>DDC</sub>	144	†	16
A14	100	D13	27	HR/W	58	V <sub>DDD</sub>	35	†	28
A15	102	D14	26	IAQ	20	V <sub>DDD</sub>	36	†	33
BCLKR	12	D15	25	INT1	59	V <sub>DDD</sub>	52	†	41
BCLKX	8	DR	65	INT2	60	V <sub>DDD</sub>	53	†	45
BDR	66	DS	112	INT3	61	V <sub>DDI</sub>	87	†	57
BDX	137	DX	136	INT4	62	V <sub>DDI</sub>	88	†	72
BFSR	11	EMU0	2	IS	113	V <sub>DDI</sub>	142	†	78
BFSX	134	EMU1/OFF	4	MP/MC	24	V <sub>DDI</sub>	143	†	83
BIO	17	FSR	67	NMI	64	V <sub>SSA</sub>	74	†	97
BR	119	FSX	132	PS	114	V <sub>SSA</sub>	92	†	101
CLKMD1	94	HAS	71	RD	106	V <sub>SSA</sub>	93	†	117
CLKMD2	130	HBIL	63	READY	14	V <sub>SSC</sub>	5	†	120
CLKMD3	121	HCNTL0	49	RS	13	V <sub>SSC</sub>	6	†	125
CLKOUT1	140	HCNTL1	51	R/W	115	V <sub>SSC</sub>	109	†	141
CLKR	68	HCS	73	STRB	116	V <sub>SSC</sub>	110		

Table A–5. Signal/Pin Assignments for the 'C57S in 144-Pin TQFP

<sup>†</sup> These pins are not connected (reserved).

D-2 In Figure D-1, change the PD pin 5 from +5V to  $V_{DD}$ .

Figure D–1. Header Signals and Header Dimensions

TMS	1	2	TRST	
TDI	3	4	GND	Header Dimensions:
PD (V <sub>DD</sub> )	5	6	No pin (key)	Pin-to-pin spacing: 0.100 in. (X,Y)
TDO	7	8	GND	Pin width: 0.025 in. square post
TCK_RET	9	10	GND	Pin length: 0.235 in., nominal
TCK	11	12	GND	
EMU0	13	14	EMU1	

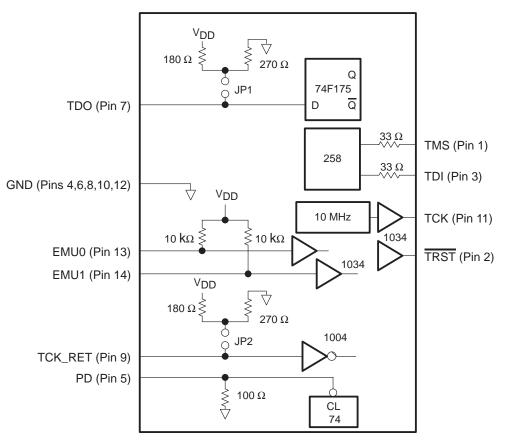
In Table D–1, change the voltage for pin 5 (the PD pin) from +5V to  $V_{DD}$ .

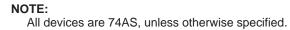
Table D–1. XDS510 Header Signal Description

Pin	Signal	State	Target State	Description
5	PD	I	0	Presence detect. Indicates that the emulation cable is connected and that the target is powered up. PD should be tied to $V_{DD}$ in the target system.

D–5 In Figure D–2, change the voltages from +5V to  $V_{DD}$ .

Figure D–2. Emulator Cable Pod Interface





D–7 In Figure D–4, change the voltages from +5V to  $V_{DD}$ .

Figure D–4. Target-System Generated Test Clock

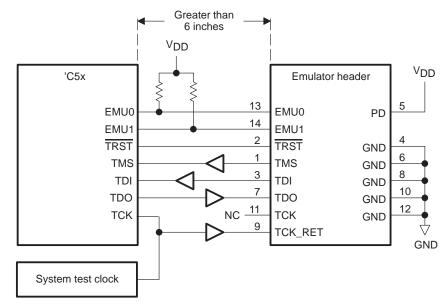
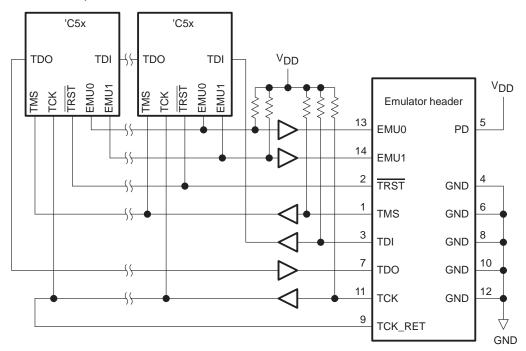




Figure D–5. Multiprocessor Connections



D–9 In Figure D–6, change the voltages from +5V to  $V_{DD}$ .

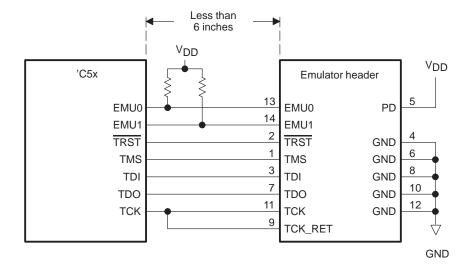
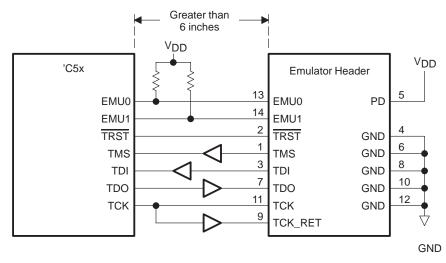


Figure D–6. Emulator Connections Without Signal Buffering

D-10 In Figure D-7, change the voltages from +5V to  $V_{DD}$ .





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